

Excellent Integrated System Limited

Stocking Distributor

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<u>Vishay Semiconductor/Diodes Division</u> <u>VS-1EFH01HM3/I</u>

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Distributor of Vishay Semiconductor/Diodes Division: Excellent Integrated System Limite

Datasheet of VS-1EFH01HM3/I - DIODE GEN PURP 100V 1A SMF

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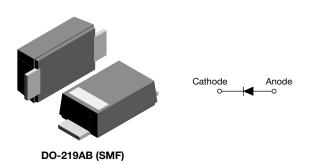


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VS-1EFH01HM3

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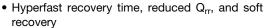
Hyperfast Rectifier, 1 A FRED Pt®



PRODUCT SUMMARY					
I _{F(AV)}	1 A				
V _R	100 V				
V _F at I _F (typ. 125 °C)	0.74 V				
t _{rr}	25 ns				
T _J max.	175 °C				
Package	DO-219AB (SMF)				

Single die

FEATURES





RoHS

COMPLIANT

FREE

- 175 °C maximum operating junction temperature
- Specified for output and snubber operation
- a Law famuard valtage dram
- Low forward voltage drop
- Low leakage current
- Meets MSL level 1, per J-STD-020, LF maximum peak of 260 °C
- AEC-Q101 qualified, meets JESD 201 class 2 whisker test
- Material categorization: for definitions of compliance please see www.vishav.com/doc?99912

DESCRIPTION / APPLICATIONS

State of the art hyperfast recovery rectifiers specifically designed with optimized performance of forward voltage drop and hyperfast recovery time.

The planar structure and the platinum doped life time control guarantee the best overall performance, ruggedness, and reliability characteristics.

These devices are intended for use in snubber, boost, lighting, piezo-injection, as high frequency rectifiers, and freewheeling diodes.

Their extremely optimized stored charge and low recovery current minimize the switching losses and reduce power dissipation in the switching element.

ABSOLUTE MAXIMUM RATINGS					
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS	
Peak repetitive reverse voltage	V_{RRM}		100	V	
Average rectified forward current	I _{F(AV)}	T _C = 160 °C ⁽¹⁾	1	۸	
Non-repetitive peak surge current	I _{FSM}	T _J = 25 °C	35	А	
Operating junction and storage temperature range	T _J , T _{Stg}		-65 to +175	°C	

Note

(1) Device on PCB with 8 mm x 16 mm soldering lands

Diode variation

ELECTRICAL SPECIFICATIONS (T _J = 25 °C unless otherwise specified)						
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS
Breakdown voltage, blocking voltage	V_{BR}, V_{R}	I _R = 100 μA	100	-	-	
Forward voltage V _F	V	I _F = 1 A	-	0.87	0.93	V
	I _F = 1 A, T _J = 125 °C	-	0.74	0.8		
Reverse leakage current	I _R	$V_R = V_R$ rated	-	-	2	
		T _J = 125 °C, V _R = V _R rated	-	0.5	8	μA
Junction capacitance	C _T	V _R = 100 V	-	5	-	pF

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DYNAMIC RECOVERY CHARACTERISTICS (T _J = 25 °C unless otherwise specified)							
PARAMETER	SYMBOL	TEST CONDITIONS		MIN.	TYP.	MAX.	UNITS
			$I_F = 1 \text{ A}, dI_F/dt = 50 \text{ A/}\mu\text{s}, V_R = 30 \text{ V}$		24	-	
Daviera vacavem tima		I _F = 0.5 A, I _R = 1 A, I _{rr} = 0.25 A		-	-	25	
Reverse recovery time	t _{rr}	T _J = 25 °C		-	16	-	ns
		T _J = 125 °C		-	23	-	
Dook receiver current		T _J = 25 °C	$I_F = 1 \text{ A}$ $dI_F/dt = 200 \text{ A/}\mu\text{s}$ $V_R = 160 \text{ V}$	-	1.6	-	۸
Peak recovery current	IRRM			2.5	-	A	
	0	T _J = 25 °C		-	13	-	
Reverse recovery charge	charge Q _{rr}	T _J = 125 °C		-	30	-	nC

THERMAL - MECHANICAL SPECIFICATIONS						
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS
Maximum junction and storage temperature range	T_J , T_{Stg}		-65	-	+175	°C
Thermal resistance, junction to case	R _{thJC}	Device mounted on PCB with 8 mm x 16 mm soldering lands	-	-	17	°C/W
Thermal resistance, junction to ambient	R _{thJA}	Device mounted on PCB with 2 mm x 3.5 mm soldering lands	-	-	140	°C/W
Approximate weight				0.015		g
Approximate weight				0.0005		oz.
Marking device		Case style SMF (DO-219AB)		M	AH	

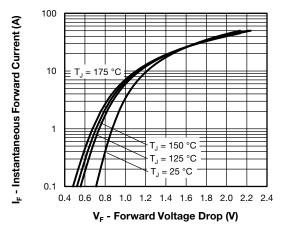


Fig. 1 - Typical Forward Voltage Drop Characteristics

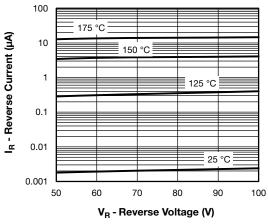


Fig. 2 - Typical Values of Reverse Current vs. Reverse Voltage

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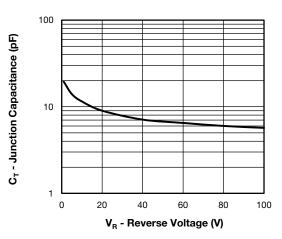


Fig. 3 - Typical Junction Capacitance vs. Reverse Voltage

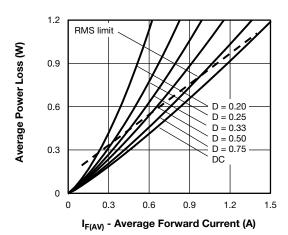


Fig. 5 - Forward Power Loss Characteristics

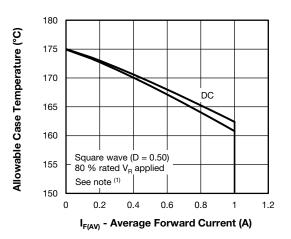


Fig. 4 - Maximum Allowable Case Temperature vs. Average Forward Current

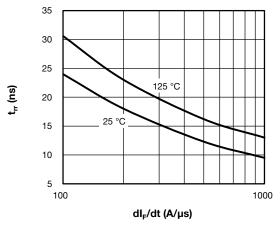


Fig. 6 - Typical Reverse Recovery Time vs. dI_F/dt

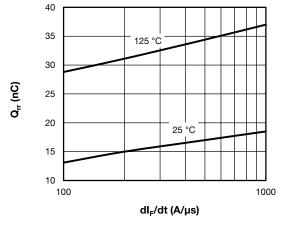


Fig. 7 - Typical Stored Charge vs. dl_F/dt

Note

 $^{(1)}$ Formula used: $T_C = T_J$ - $(Pd + Pd_{REV}) \times R_{th,JC};$ Pd = forward power loss = $I_{F(AV)} \times V_{FM}$ at $(I_{F(AV)}/D)$ (see fig. 5); $Pd_{REV} =$ inverse power loss = $V_{R1} \times I_{R}$ (1 - D); I_{R} at $V_{R1} =$ rated V_{R}

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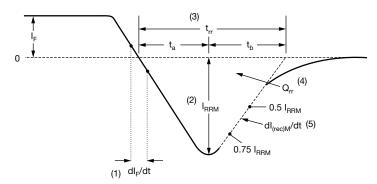
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- dl_F/dt rate of change of current through zero crossing
- (2) I_{RRM} peak reverse recovery current
- (3) $\rm t_{rr}$ reverse recovery time measured from zero crossing point of negative going $\rm l_F$ to point where a line passing through 0.75 $\rm l_{RRM}$ and 0.50 $\rm l_{RRM}$ extrapolated to zero current.
- (4) \mathbf{Q}_{rr} area under curve defined by \mathbf{t}_{rr} and \mathbf{I}_{RRM}

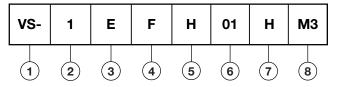
$$Q_{rr} = \frac{t_{rr} \times I_{RRM}}{2}$$

(5) $dl_{(rec)M}/dt$ - peak rate of change of current during t_b portion of t_{rr}

Fig. 8 - Reverse Recovery Waveform and Definitions

ORDERING INFORMATION TABLE

Device code



- 1 Vishay Semiconductors product
- 2 Current rating (1 = 1 A)
- 3 Circuit configuration:

E = single diode

- F = SMF package
- **5** Process type,

H = hyperfast recovery

- 6 Voltage code (01 = 100 V)
- 7 H = AEC-Q101 qualified
- 8 M3 = halogen-free, RoHS-compliant, and terminations lead (Pb)-free

ORDERING INFORMATION (Example)					
PREFERRED P/N	QUANTITY PER REEL	MINIMUM ORDER QUANTITY	PACKAGING DESCRIPTION		
VS-1EFH01HM3/I	10 000	10 000	13"diameter plastic tape and reel		

LINKS TO RELATED DOCUMENTS				
Dimensions	www.vishay.com/doc?95572			
Part marking information	www.vishay.com/doc?95618			
Packaging information	www.vishay.com/doc?95577			
SPICE model	www.vishay.com/doc?96012			

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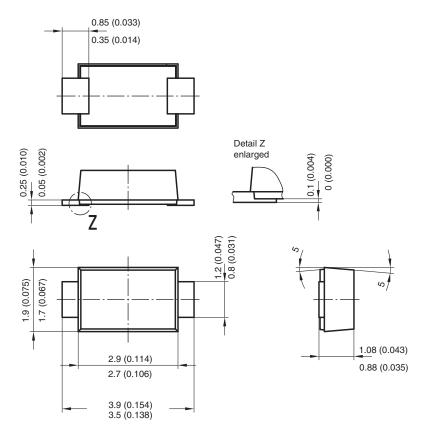


Outline Dimensions

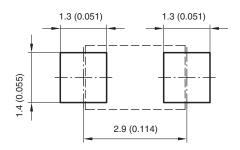
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DO-219AB (SMF)

DIMENSIONS in millimeters (inches)



Foot print recommendation:



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